

80A 300V Fast recovery diode

1 Description

80A, 300V Ultrafast Diodes The products are made by GPP process They have a low forward. These devices are intended for use as energy steering/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications.

2 Features

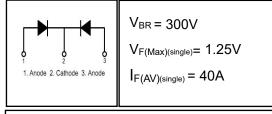
- Low forward voltage drop
- Glass Passivated Die Construction
- Low leakage current
- High reliability
- High forward surge current capability

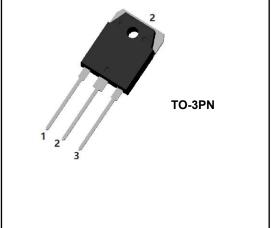
3 Applications

- Switching Power Supply
- Power Switching Circuits
- Inverter power supply

4 install

- Recommendedtorque value (TO-247): 0.8 N.m.
- Recommendedtorque value (TO-3PN/3P): 0.8 N.m
- Maximum torque value (TO-247): 1.2 N.m
- Maximum torque value(TO-3PN/3P): 1.1 N.m





5 Electrical Characteristics

5.1 Absolute Maximum Ratings (Tc=25 $^{\circ}$ C,unless otherwise noted)

PARAMETER		SYMBOL	VALUE	UNIT
Peak Repetitive Reverse Voltage		V_{RRM}	300	V
Working Peak Reverse Voltage		V_{RWM}	300	V
DC Blocking Voltage		V _R	300	V
Average Rectified Forward Current(single)		I _{F(AV)}	40	Α
Average Rectified Forward Current(double)			80	Α
Repetitive Peak Surge Current(single)		I _{FRM}	50	Α
Nonrepetitive Peak Surge Current(single)	tp=8.3ms	I _{FSM}	400	Α
Avalanche Energy(single)	L=1mH	E _{AS}	100	mJ
Operating Junction Temperature Range		Tj	- 55∼150	$^{\circ}$
Storage Temperature Range		T _{stg}	-55∼150	$^{\circ}$

5.2 Thermal Characteristics

PARAMETER	SYMBOL	VALUE	UNIT
Thermal Resistance, Junction to Case-sink	R _{thJC}	0.75	°C/W



5.3 Electrical Characteristics

(Tc=25[°]C,unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Maximum Instantaneous		$I_F = 30A$	-	1.00	1.15	V
Forward Voltage	V _F	I _F = 30A, T _C = 150 °C	-	0.88		V
		I _F = 40A	-	1.10	1.25	V
Maximum Instantaneous	I _R	V _R = 300V	-	-	10	uA
Reverse		V _R = 300V, T _C = 150°C	-	-	2.0	mA
Maximum Reverse	t _{rr}	V _R =30V IF=1A -dI/dt=50A/us	-	36	50	ns
Recovery Time						
Total capacitance	C _{tot}	V _R =0V f=1MHz	-	710	-	pF
DC Blocking Voltage	V_{BR}	I _R =100uA	300	350	-	V

DEFINITIONS

VF = Instantaneous forward voltage (pw = 300μ s, D = 2%).

IR = Instantaneous reverse current.

 $R\theta JC$ = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

6 Typical characteristics diagrams

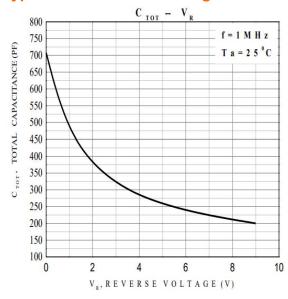


FIGURE 1. Total capacitance vs Voltage

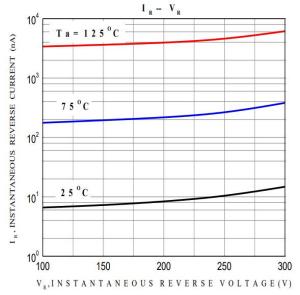


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE



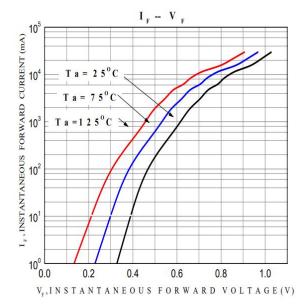


FIGURE 3. FORWARD CURRENT vs FORWARD VOLTAGE

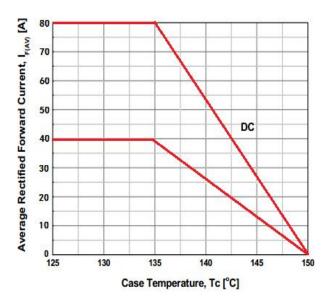


FIGURE 4. CURRENT DERATING CURVE

7 Typical Test Circuit and Waveform

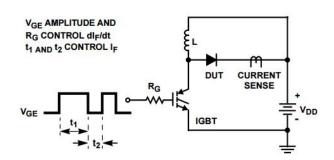


FIGURE 5. trr TEST CIRCUIT

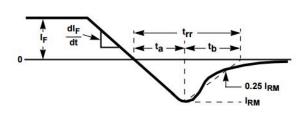


FIGURE 6. trr WAVEFORMS AND DEFINITIONS

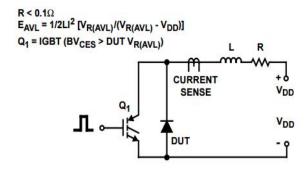


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT FIGURE

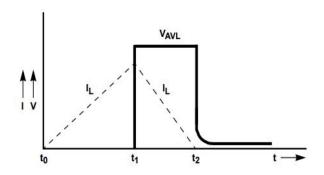


FIGURE8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

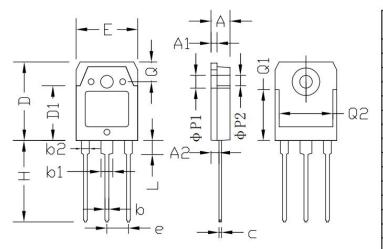


8 Product Specifications and Packaging Models

Product Model	Package Type	Mark Name	RoHS	Package	Quantity
MUR80G30NCT	TO-3PN	MUR80G30NCT	Pb-free	Tube	300/box

9 Dimensions

TO-3PN PACKAGE OUTLINE DIMENSIONS



C-1-1	Dimensions In	Millimeters	Dimensions	In Inches
Symbol	min.	max.	min.	max.
A	4. 60	5. 00	0. 181	0. 197
A1	1. 45	1.65	0.057	0.065
A2	2. 20	2.60	0.087	0. 102
b	0.80	1.20	0.032	0.047
b1	2.80	3. 20	0.110	0.126
b2	1.80	2. 20	0.071	0.087
С	0.55	0.75	0.022	0.030
D	19. 20	19. 80	0. 756	0. 780
D1	13. 10	14.70	0.516	0.578
Е	15. 40	15. 80	0.607	0.623
е	5. 4	5 TYP	0. 21	5 TYP
Н	19. 80	20.50	0. 780	0.807
L	3. 20	3. 70	0. 126	0. 146
ФР1	3. 20	0 TYP	0. 12	26 TYP
ФР2	3. 5	0 TYP	0.13	88 TYP
Q	5. 0	0 TYP	0. 19	7 TYP
Q1	12. 4	O TYP	0.48	88 TYP
Q2	12.6		0.496	8758

10 Attentions

- Jiangsu Donghai Semiconductor Co.,Ltd.. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of Jiangsu Donghai Semiconductor Co.,Ltd. products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

11 Appendix

Revision history:

Date	REV.	Description	Page
2022.8.12	1.0	Original	